# Semiconductors, Junctions, and MOSFET Overview





## Introduction

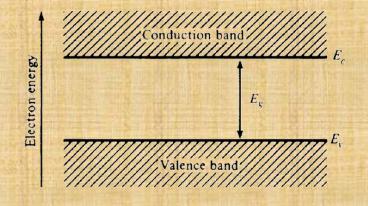
- Introducing semiconductors
- > Evaluation of mobile carrier concentration
- Considering the mechanisms of current transport
- Contacts between different materials and the electrostatic potentials established in such contacts
- >pn contact (junction)
- Overview of MOS transistor



- Intrinsic Semiconductors, Free Electrons, and Holes
  - Equilibrium
  - Pure Silicon
    - o Lattice constant: 0.5 nm
    - o Crystal lattice and contains approximately 5 x 1022 atoms/cm3
    - o Bohr Model, Free Electron and effect of Temperature
    - Hole concept Valance electron movement
    - Carrying Charge mechanism
      - > The motion of free electrons about the lattice
      - The motion of valance electrons from bond to bond corresponding to a motion of "vacancies" or holes
    - Charge neutrality
    - Recombination

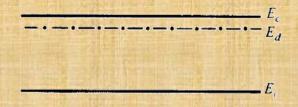


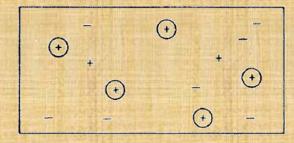
- Energy Bands
  - Band gap energy E<sub>g</sub>
  - Conduction energy
  - Valance energy
  - Insulator and Conductor band gap energy
  - Charge neutrality n<sub>i=</sub>p<sub>i</sub>
  - Free carrier concentration temperature and material dependency





- Extrinsic Semiconductors
  - Impurities and doping
  - Donor and acceptor atoms
  - Introducing E<sub>d</sub> and E<sub>a</sub>
  - $N_0 \times P_0 = ni^2$
  - Donor Atoms (N<sub>d</sub>): phosphorus, arsenic, and antimony
  - Acceptor Atoms (N<sub>a</sub>): boron, gallium, and indium
  - Temperature effect on donor/Acceptor atoms
  - Carrier concentration
  - Majority and Minority Carriers
  - Degeneracy
  - N type and P type Semiconductors







- Equilibrium in the Absence of Electric Field
  - General Carrier densities

$$p_0 = n_i e^{(E_i - E_f)/kT}$$

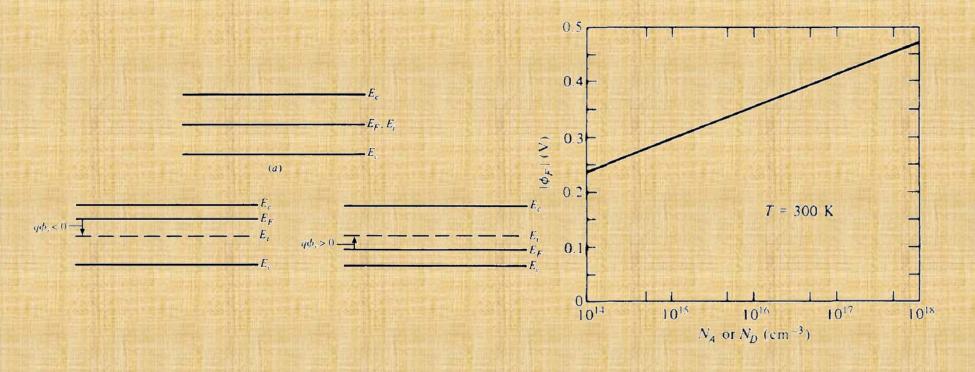
$$n_0 = n_i e^{(E_f - E_i)/kT}$$

- Fermi and Intrinsic Energies definitions
- $\bullet$   $\Phi_f$  and  $\Phi_T$  definition

$$\phi_f = \frac{E_i - E_f}{q}$$

$$\phi_T = \frac{kT}{q}$$







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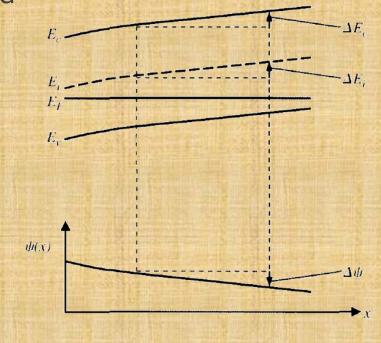
- Equilibrium in the Presence of Electric Field
  - Within electric field 2 contact MOS
  - Charge neutrality n, p product remain ni<sup>2</sup>

$$p = n_i e^{(E_i - E_f)/kT}$$

$$n = n_i e^{(E_f - E_i)/kT}$$

- Zero current flow
- Electrostatic potential

$$\psi(x) = E_i(x)/-q$$

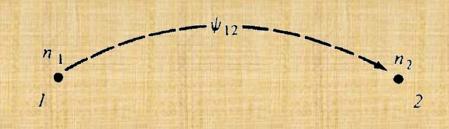




Electrostatic potential deference effects

$$\frac{n_1}{n_2} = \exp\left(\frac{\psi_{12}}{\phi_T}\right)$$

$$\frac{p_1}{p_2} = \exp\left(\frac{\psi_{12}}{\phi_T}\right)$$



Important result

$$n_1p_1 = n_2p_2$$



- Nonequilibrium; Quasi-Fermi Levels
  - Energy exchange between the semiconductor and the external world – Like using battery
  - Fermi level is not constant -- imref
  - Charge neutrality space charge (Depletion region)

$$p = n_i e^{(E_i - E_{fp})/kT}$$

$$n = n_i e^{(E_{fn} - E_i)/kT}$$

■ In equilibrium E<sub>fn</sub>=E<sub>fp</sub>=E<sub>f</sub> and np=ni<sup>2</sup>



- •Relations between <u>Charge Density</u>, <u>Electric Field</u>, and <u>Potential</u>; Poisson's Equation
  - charge density (charge concentration per unit volume)
    - 1. holes, which contribute a charge density of (+q)p
    - 2. free electrons, with contribution (-q)n
    - 3. ionized donor atoms, with contribution  $(+q)N_D(!)$
    - 4. Ionized acceptor atoms, with contribution  $(-q)N_A(!)$
- Total charge density:  $\rho = q(p n + N_D N_A)$



- Charge density...
  - Regularly N<sub>A</sub>=0 or N<sub>D</sub>=0
  - In fab. Process both present, why?
  - Charge neutrality
  - Locally natural region :  $p_0 n_0 = -(N_D N_A)$ ,  $p_0 n_0 = n_i^2$
- Gauss Law

$$\frac{dE(x)}{dx} = \frac{\rho}{\varepsilon_s}$$

In the presence of electric fields, the charge density ρ can vary from point to point, why?



- Gauss law....

By integrating both sides of Gauss Eq. from an arbitrary point 
$$y_0$$
 to a point  $y$ , we obtain 
$$E(y) = E(y_0) + \frac{1}{\varepsilon_s} \int\limits_{y_0}^y \rho(y') dy'$$

- We can do this for both the pn junction and the MOS structure
- Poisson equation
  - Electric Field and Potential relationship

$$E(x) = -\frac{d\psi}{dx}$$

$$\psi(y) = \psi(y_0) - \int_{y_0} E(y')dy'$$

$$\frac{d^2\psi(x)}{dx^2} = -\frac{\rho(y)}{\varepsilon_s}$$

